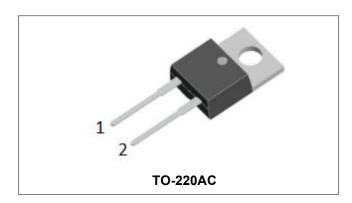






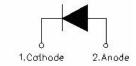
## **MBR1020 SCHOTTKY RECTIFIER**



#### **Features**

- 125 °C T<sub>J</sub> operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced
- mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage	$V_{RRM}$ $V_{RWM}$	-	20	V
DC Blocking Voltage	V <sub>R</sub>		_	-
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=75°C, rectangular wave form	10	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse	150	A

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 10A, Pulse, T <sub>J</sub> = 25 °C	0.5	0.55	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_{R_1} T_J = 25 ^{\circ}\text{C}$	0.02	0.2	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 100 °C	4	50.0	mA
Series Inductance	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 μs, duty cycle < 2%



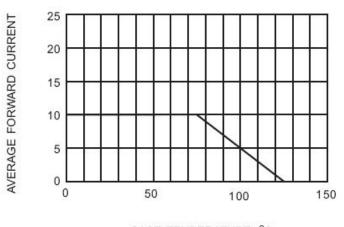




## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +125	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	Rejc	DC operation	3	°C/W
Approximate Weight	wt	-	1.6	g
Case Style	TO-220AC			

## **Ratings and Characteristics Curves**



CASE TEMPERATURE, °C

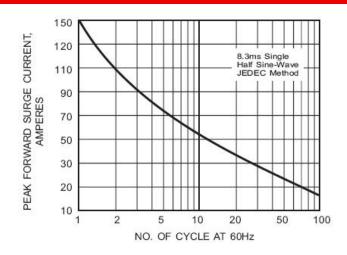


Fig.1-Forward Current Derating Curve

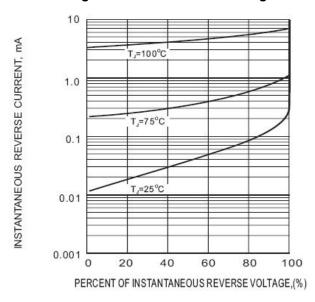


Fig.3-Typical Reverse Characteristic

Fig.2-Maximum Non-Repetitive Surge Current

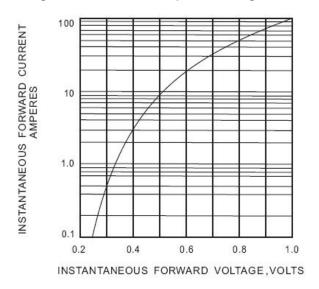


Fig.4-Typical Instantaneous Forward Characteristic

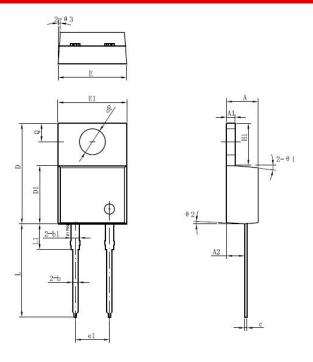
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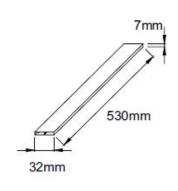


### **Mechanical Dimensions TO-220AC**

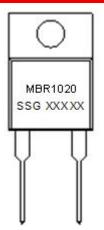


Symbol	Dimensions in millimeters				
	Min.	Typical	Max.		
Α	4.47	4.70	4.85		
A1	1.17	1.27	1.37		
A2	2.52	2.69	2.89		
b	0.71	0.81	0.96		
b1	1.17	1.27	1.37		
С	0.31	0.38	0.61		
D	14.64	14.94	15.24		
D1	8.50	8.07	8.90		
E	10.01	10.16	10.31		
E1	9.98	10.18	10.38		
e1	4.98	5.08	5.18		
H1	6.04	6.24	6.44		
L	13.00	13.86	14.08		
L1	3.56	3.80	3.96		
ФР	3.74	3.84	4.04		
Q	2.54	2.74	2.94		
Θ1		5°			
Θ2		4°			
Θ3		4°			

### **Tube Specification**



# **Marking Diagram**



Where XXXXX is YYWWL

MBR = Device Type 10 = Forward Current (10A) 20 = Reverse Voltage(20V) SSG = SSG YY = Year

YY = Year WW = Week L = Lot Number

**Cautions:** Molding resin Epoxy resin UL:94V-0

## **Ordering Information**

Device	Package	Shipping	
MBR1020	TO-220AC (Pb-Free)	50 pcs/ tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging Specification.

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